

UNR511x Series (UN511x Series)

Silicon PNP epitaxial planar type

For digital circuits

■ Features

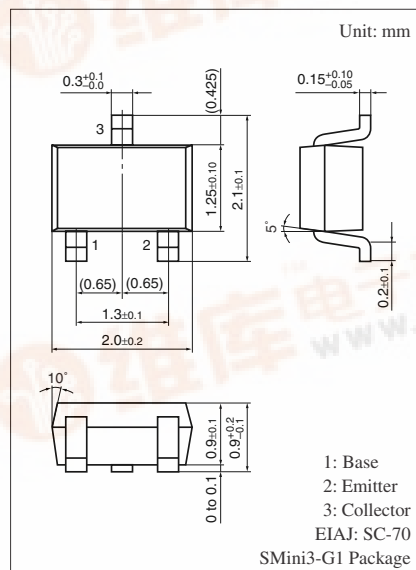
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts
- S-Mini type package, allowing automatic insertion through the tape/ magazine packing

■ Resistance by Part Number

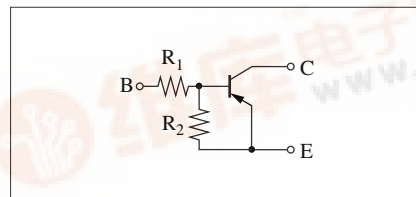
	Marking symbol	(R ₁)	(R ₂)
• UNR5110 (UN5110)	6L	47 kΩ	—
• UNR5111 (UN5111)	6A	10 kΩ	10 kΩ
• UNR5112 (UN5112)	6B	22 kΩ	22 kΩ
• UNR5113 (UN5113)	6C	47 kΩ	47 kΩ
• UNR5114 (UN5114)	6D	10 kΩ	47 kΩ
• UNR5115 (UN5115)	6E	10 kΩ	—
• UNR5116 (UN5116)	6F	4.7 kΩ	—
• UNR5117 (UN5117)	6H	22 kΩ	—
• UNR5118 (UN5118)	6I	0.51 kΩ	5.1 kΩ
• UNR5119 (UN5119)	6K	1 kΩ	10 kΩ
• UNR511D (UN511D)	6M	47 kΩ	10 kΩ
• UNR511E (UN511E)	6N	47 kΩ	22 kΩ
• UNR511F (UN511F)	6O	4.7 kΩ	10 kΩ
• UNR511H (UN511H)	6P	2.2 kΩ	10 kΩ
• UNR511L (UN511L)	6Q	4.7 kΩ	4.7 kΩ
• UNR511M (UN511M)	EI	2.2 kΩ	47 kΩ
• UNR511N (UN511N)	EW	4.7 kΩ	47 kΩ
• UNR511T (UN511T)	EY	22 kΩ	47 kΩ
• UNR511V (UN511V)	FC	2.2 kΩ	2.2 kΩ
• UNR511Z (UN511Z)	FE	4.7 kΩ	22 kΩ

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-50	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Collector current	I _C	-100	mA
Total power dissipation	P _T	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)		V _{CBO}	I _C = −10 μA, I _E = 0	−50			V
Collector-emitter voltage (Base open)		V _{CEO}	I _C = −2 mA, I _B = 0	−50			V
Collector-base cutoff current (Emitter open)		I _{CBO}	V _{CB} = −50 V, I _E = 0			− 0.1	μA
Collector-emitter cutoff current (Base open)		I _{CEO}	V _{CE} = −50 V, I _B = 0			− 0.5	μA
Emitter-base cutoff current (Collector open)	UNR5110/5115/5116/5117	I _{EBO}	V _{EB} = −6 V, I _C = 0			− 0.01	mA
	UNR5113					− 0.1	
	UNR5112/5114/511D/ 511E/511M/511N/511T					− 0.2	
	UNR511Z					− 0.4	
	UNR5111					− 0.5	
	UNR511F/511H					− 1.0	
	UNR5119					− 1.5	
	UNR5118/511L/511V					− 2.0	
Forward current transfer ratio	UNR511V	h _{FE}	V _{CE} = −10 V, I _C = −5 mA	6		20	—
	UNR5118/511L			20			
	UNR5119/511D/511F/511H			30			
	UNR5111			35			
	UNR5112/511E			60			
	UNR511Z			60		200	
	UNR5113/5114/511M			80			
	UNR511N/511T			80		400	
	UNR5110*/5115*/5116*/5117*			160		460	
Collector-emitter saturation voltage		V _{CE(sat)}	I _C = −10 mA, I _B = − 0.3 mA			− 0.25	V
UNR511V			I _C = −10 mA, I _B = −1.5 mA				
Output voltage high-level		V _{OH}	V _{CC} = −5 V, V _B = − 0.5 V, R _L = 1 kΩ	−4.9			V
Output voltage low-level		V _{OL}	V _{CC} = −5 V, V _B = −2.5 V, R _L = 1 kΩ			− 0.2	V
UNR5113			V _{CC} = −5 V, V _B = −3.5 V, R _L = 1 kΩ				
UNR511D			V _{CC} = −5 V, V _B = −10 V, R _L = 1 kΩ				
UNR511E			V _{CC} = −5 V, V _B = −6 V, R _L = 1 kΩ				
Transition frequency		f _T	V _{CB} = −10 V, I _E = 1 mA, f = 200 MHz		80		MHz
UNR5116			V _{CB} = −10 V, I _E = 2 mA, f = 200 MHz		150		
Input resistance	UNR5118	R ₁		−30%	0.51	+30%	kΩ
	UNR5119				1.0		
	UNR511H/511M/511V				2.2		
	UNR5116/511F/511L 511N/511Z				4.7		
	UNR5111/5114/5115				10		
	UNR5112/5117/511T				22		
	UNR5110/5113/511D/511E				47		
Resistance ratio	UNR511M	R ₁ /R ₂			0.047		—
	UNR511N				0.1		
	UNR5118/5119			0.08	0.10	0.12	
	UNR511Z				0.21		

■ Electrical Characteristics (continued) $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

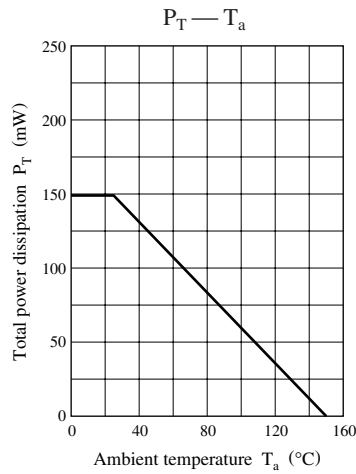
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Resistance ratio	UNR5114			0.17	0.21	0.25	
	UNR511H			0.17	0.22	0.27	
	UNR511T				0.47		
	UNR511F			0.37	0.47	0.57	
	UNR511V				1.0		
	UNR5111/5112/5113/511L			0.8	1.0	1.2	
	UNR511E			1.70	2.14	2.60	
	UNR511D			3.7	4.7	5.7	

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

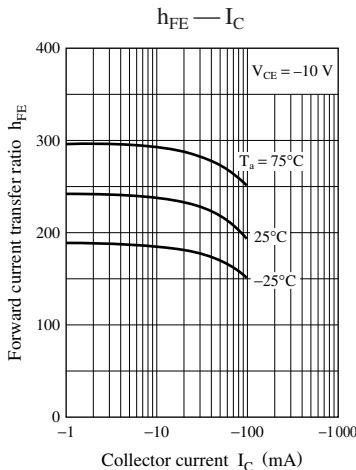
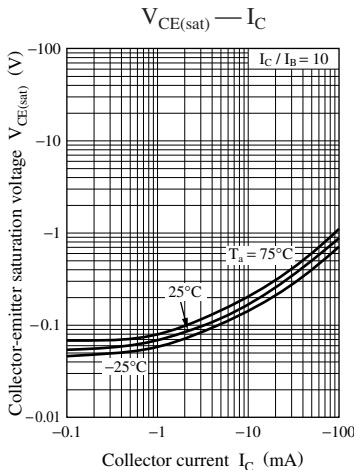
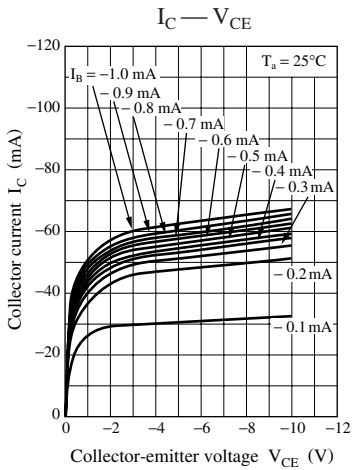
2. *: Rank classification

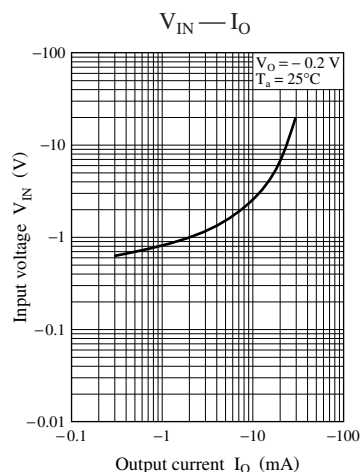
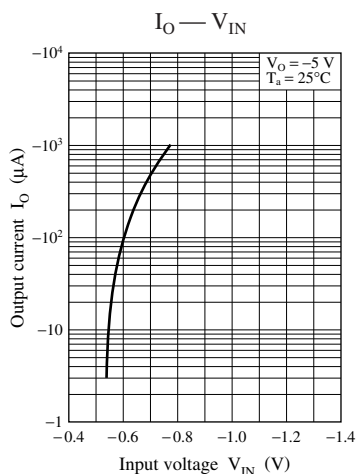
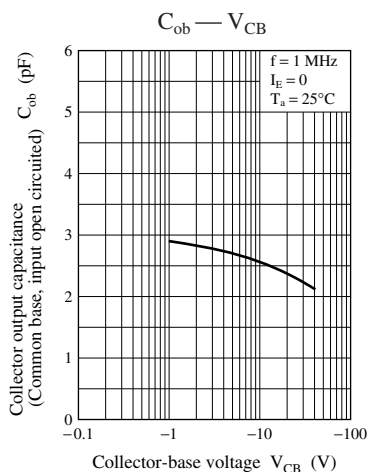
Rank	Q	R	S	No-rank
h_{FE}	160 to 260	210 to 340	290 to 460	160 to 460

Common characteristics chart

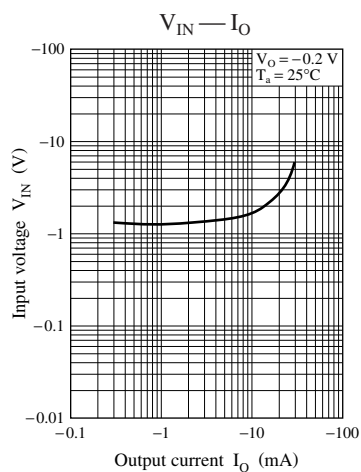
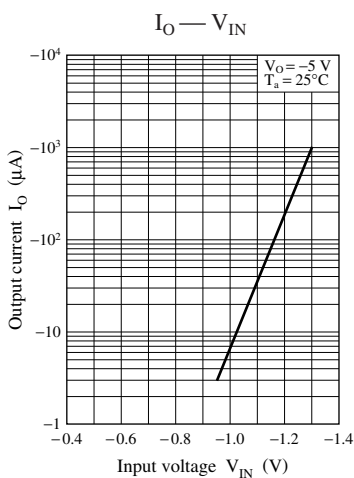
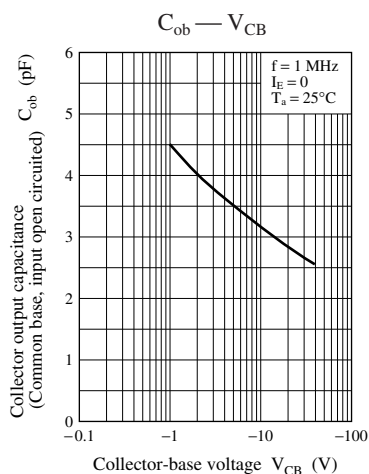
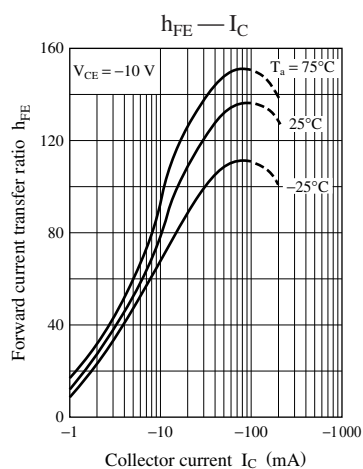
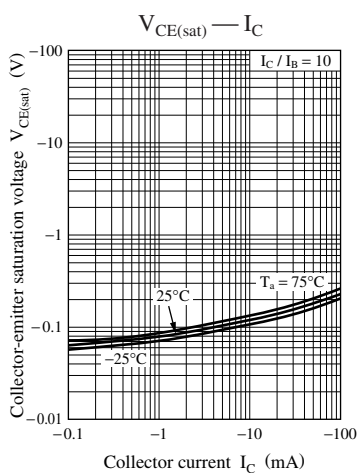
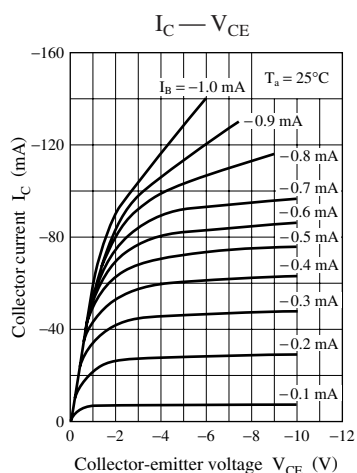


Characteristics charts of UNR5110

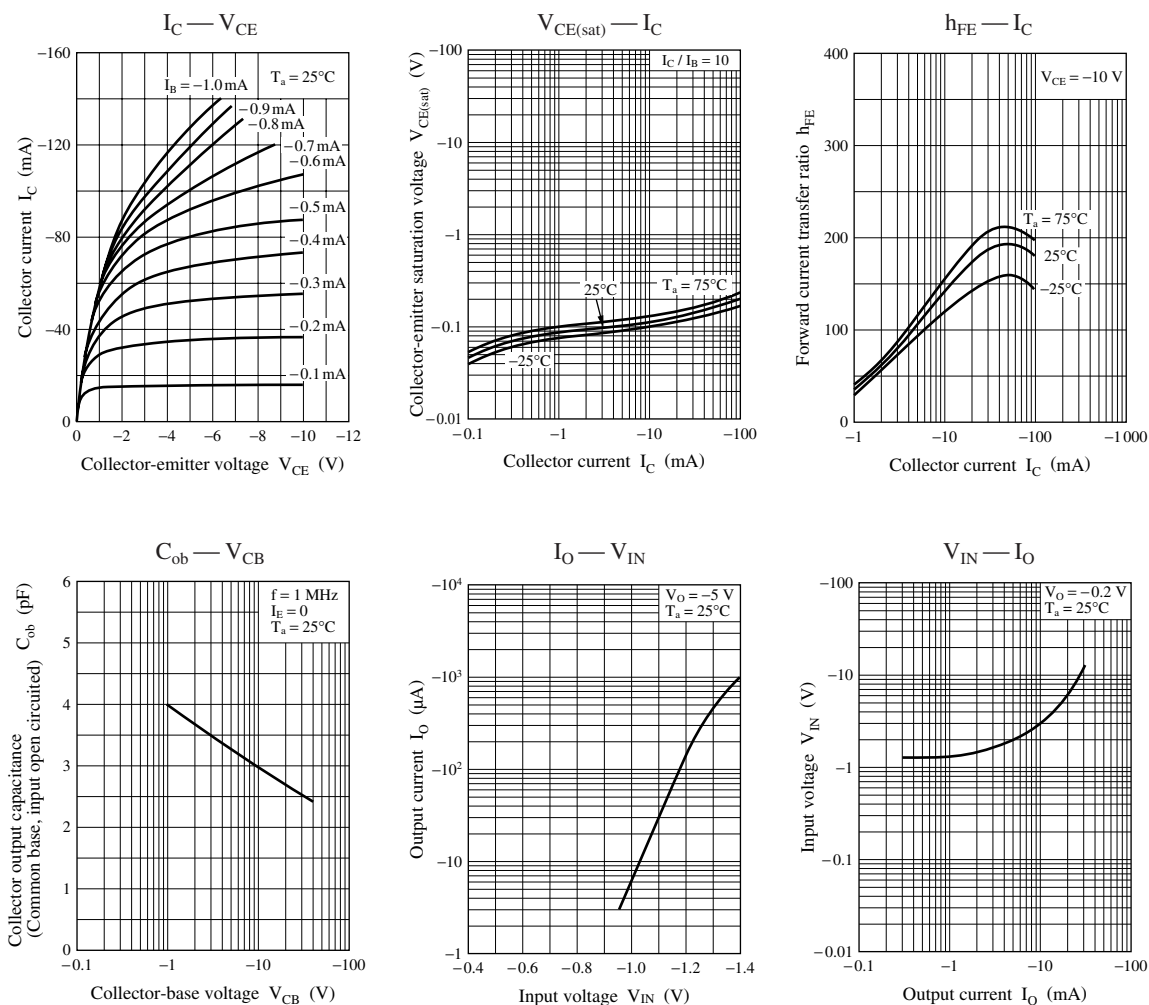




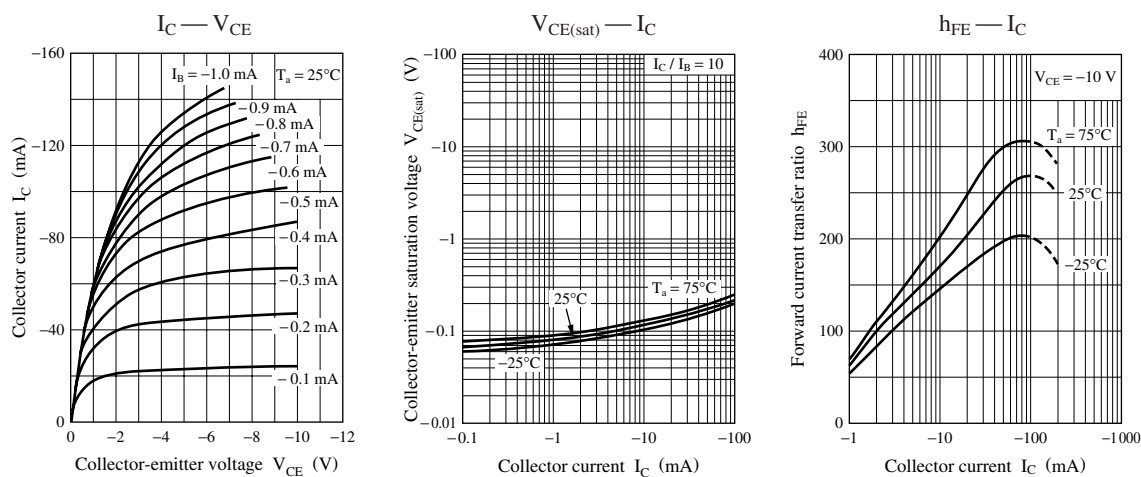
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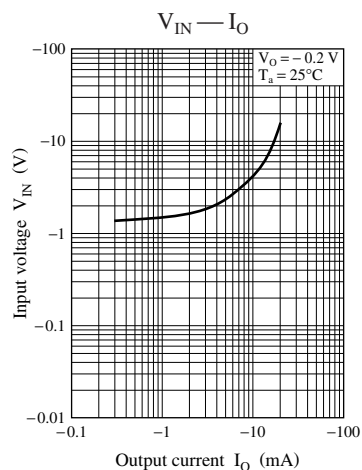
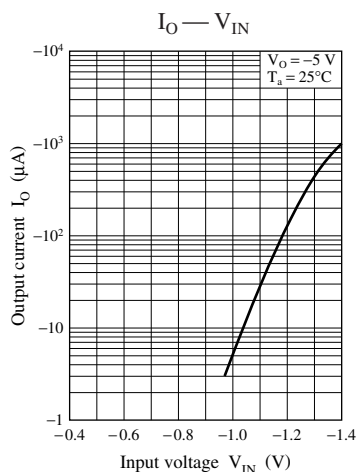
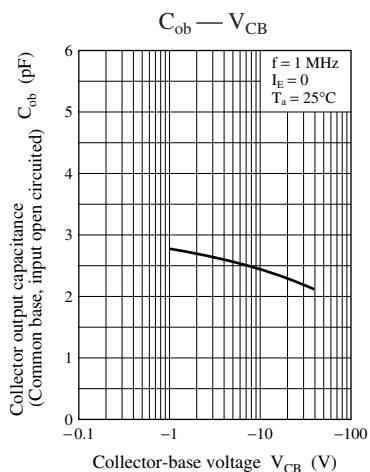


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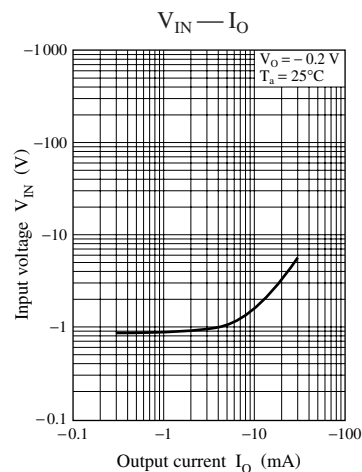
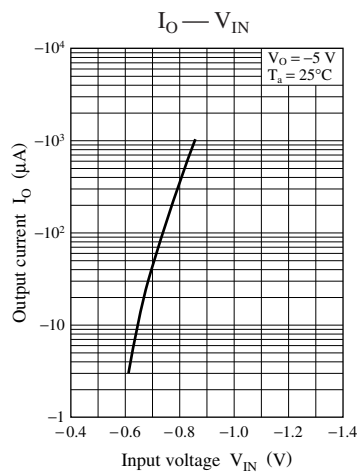
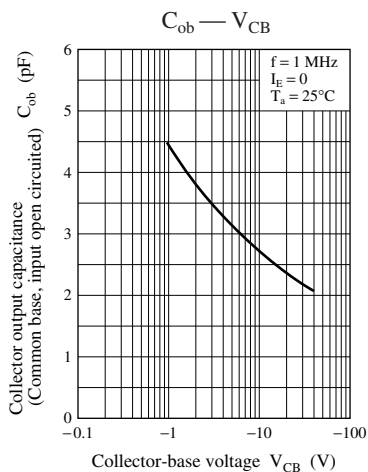
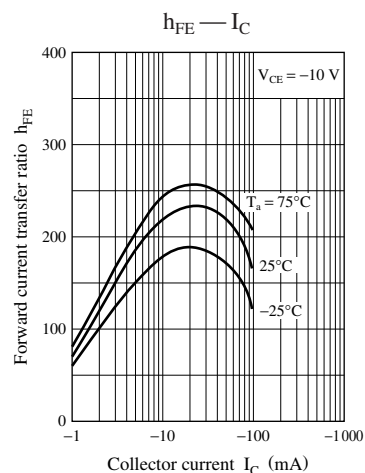
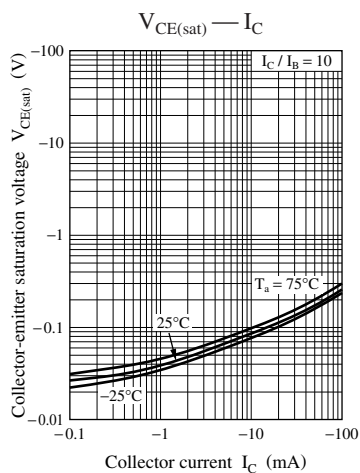
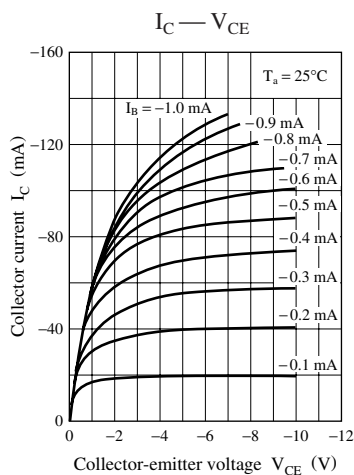


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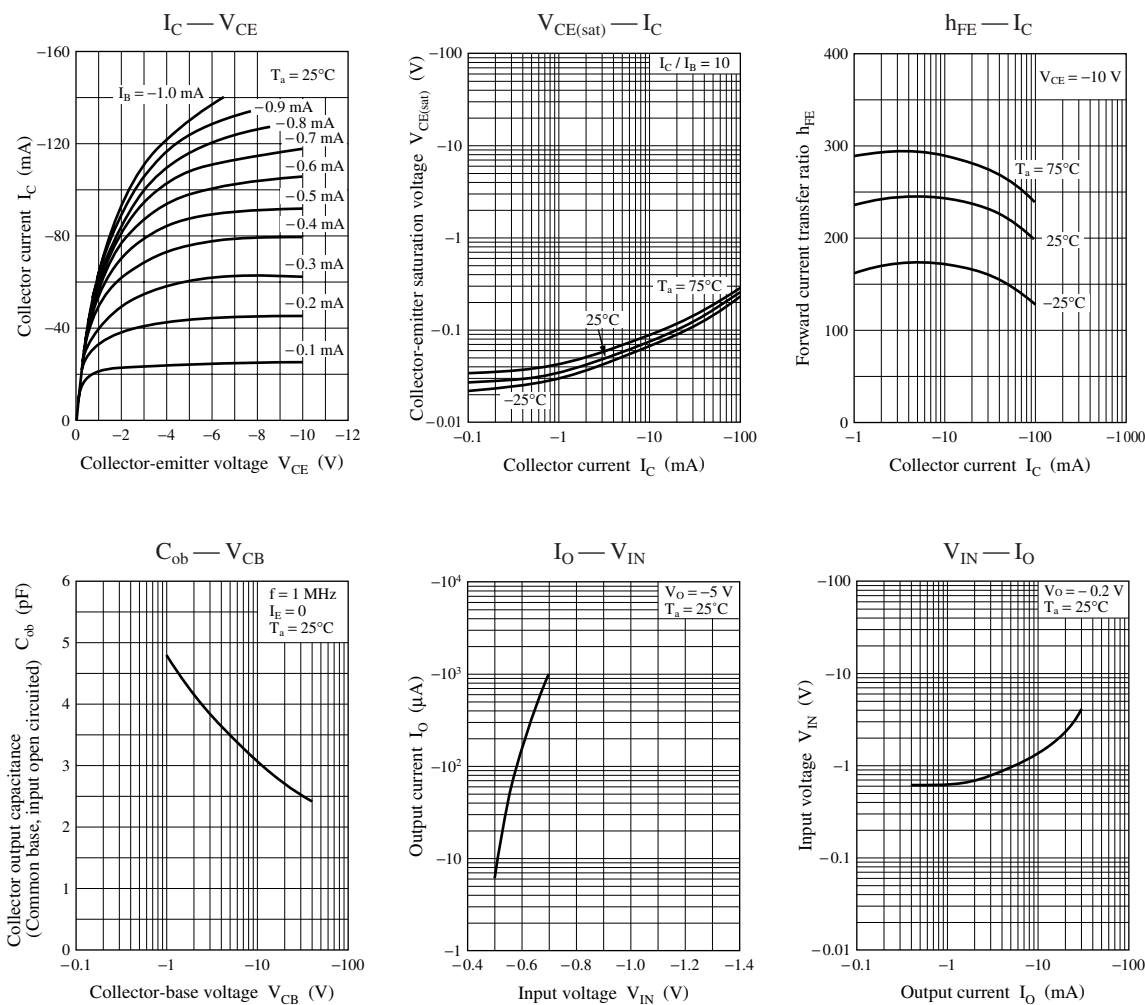




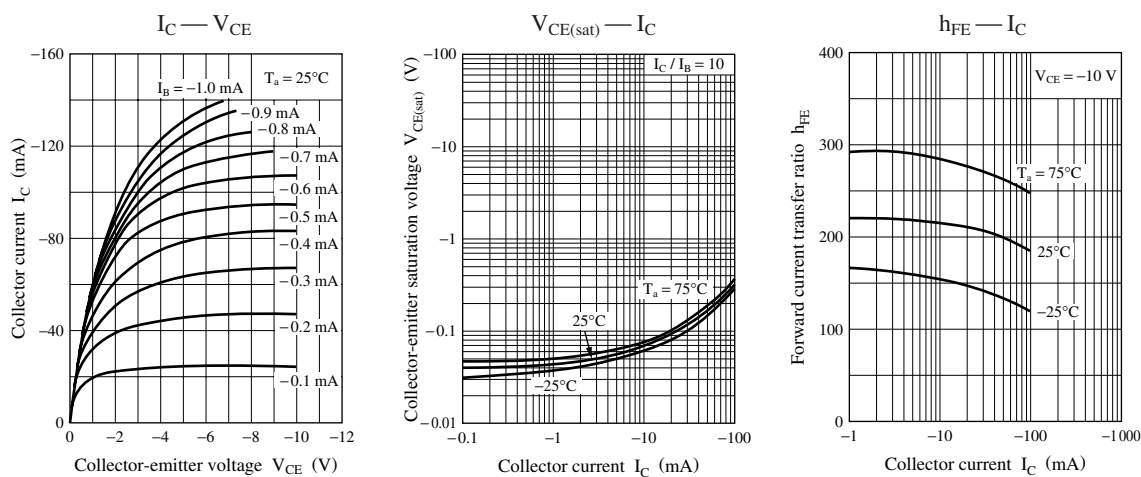
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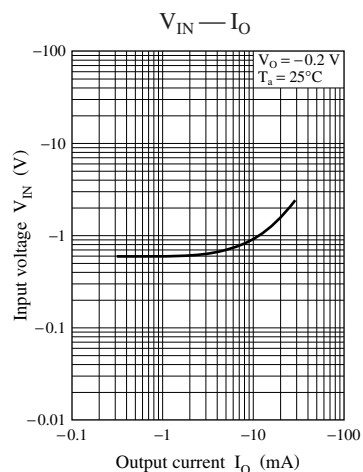
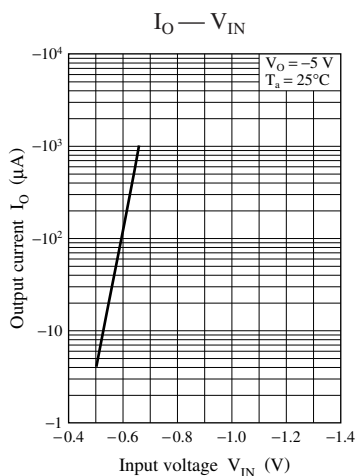
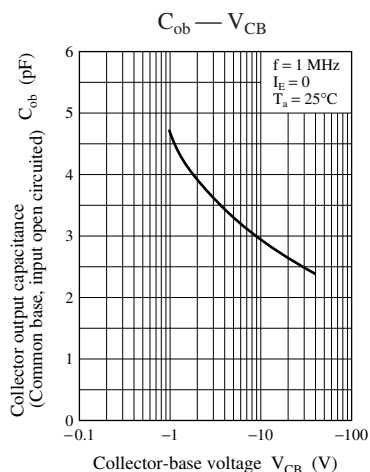


Characteristics charts of UNR5115

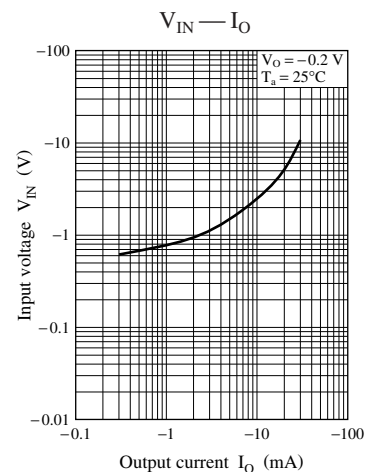
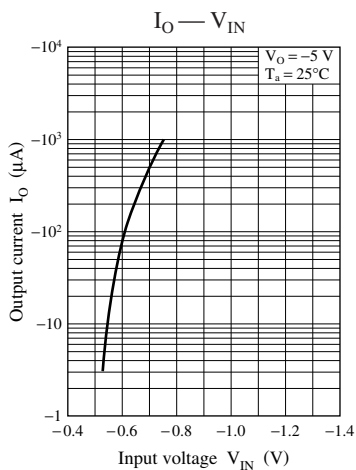
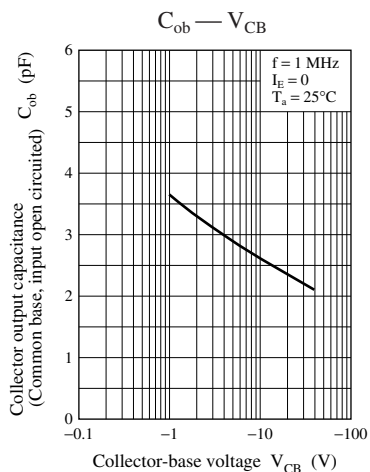
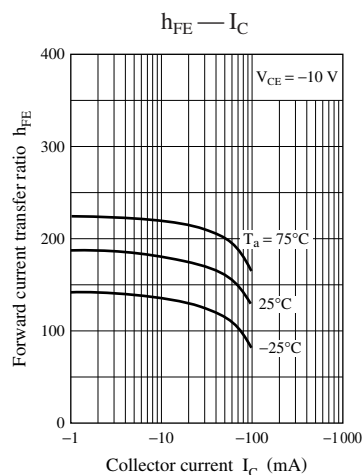
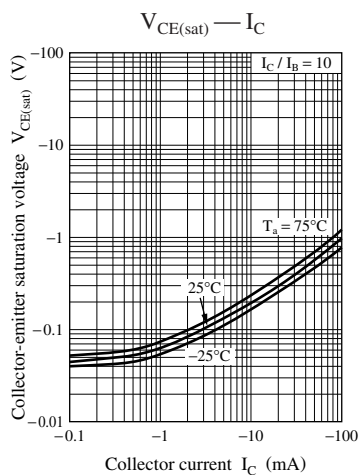
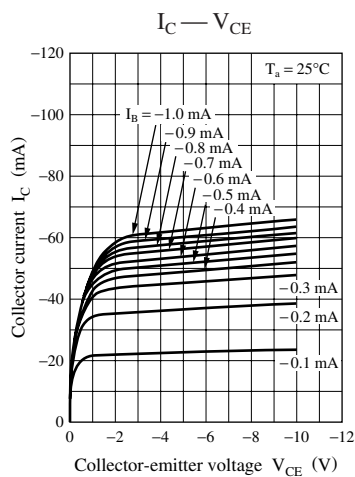


Characteristics charts of UNR5116

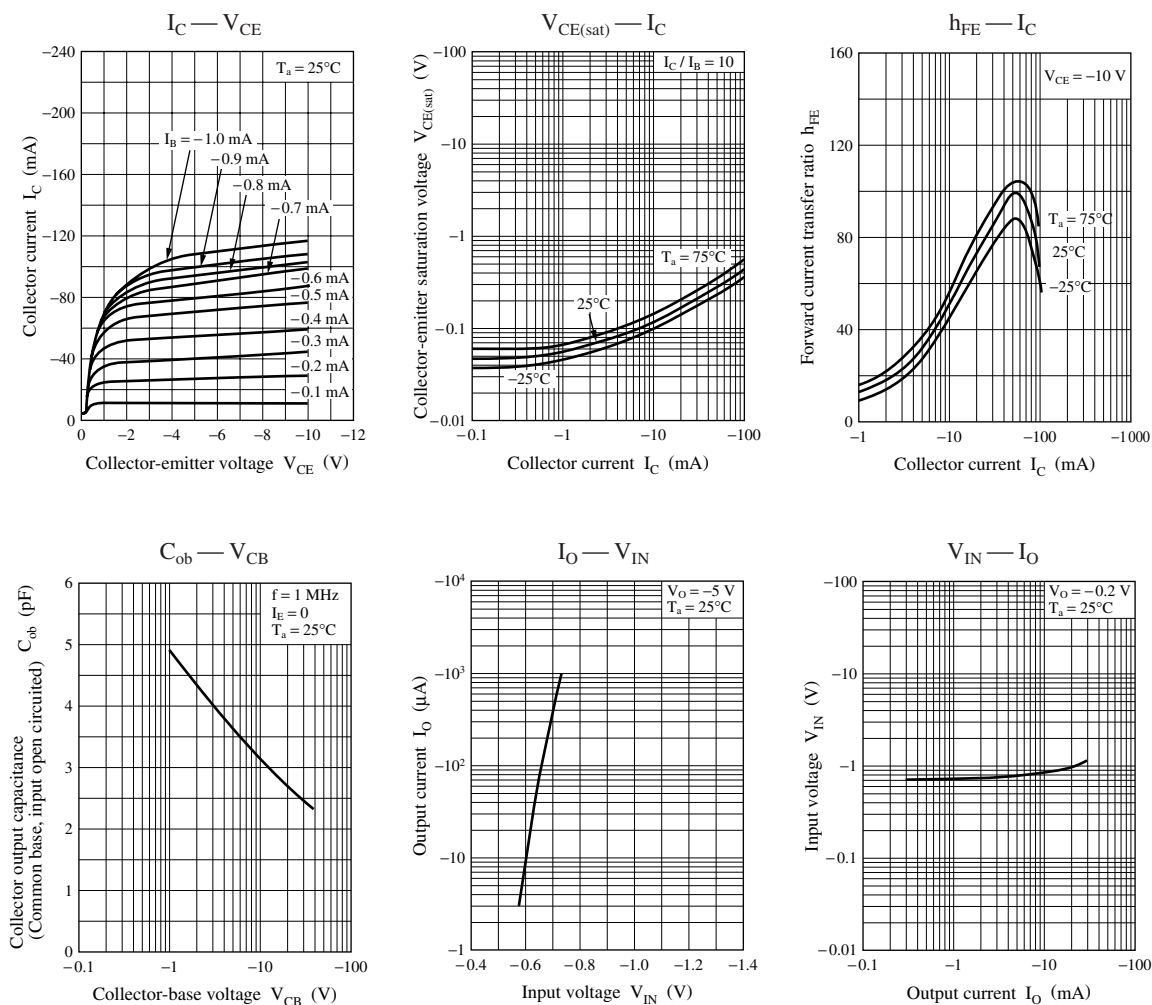




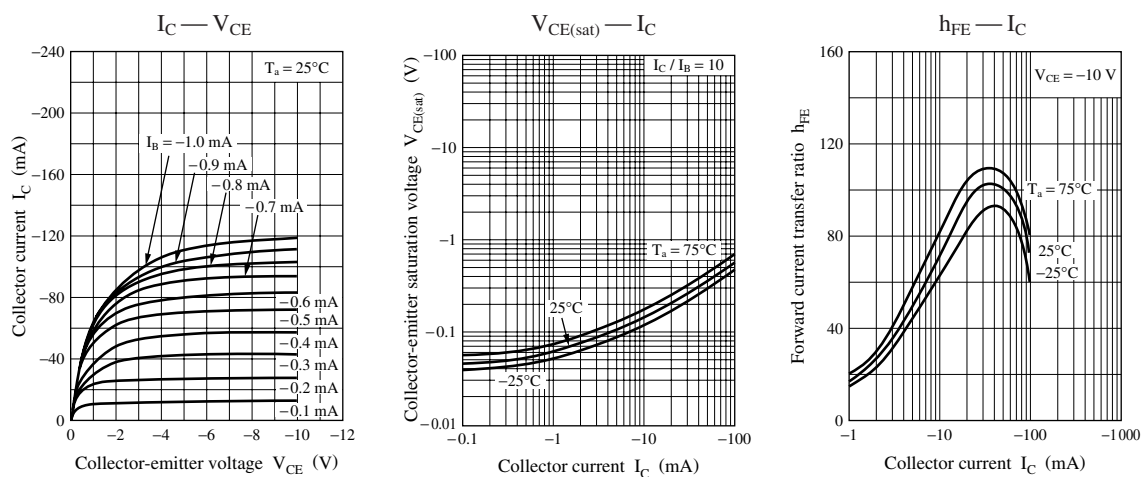
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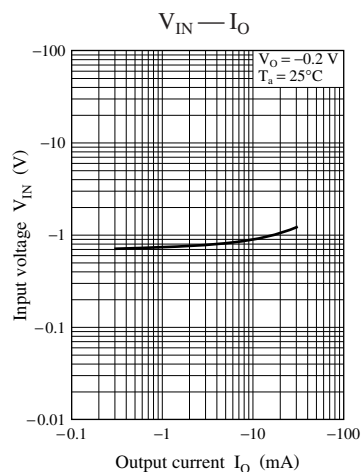
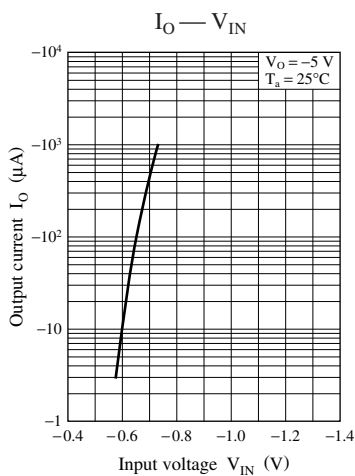
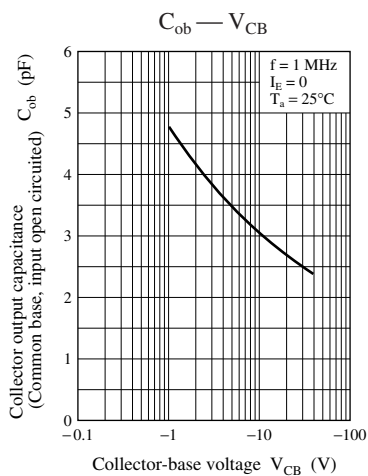


Characteristics charts of UNR5118

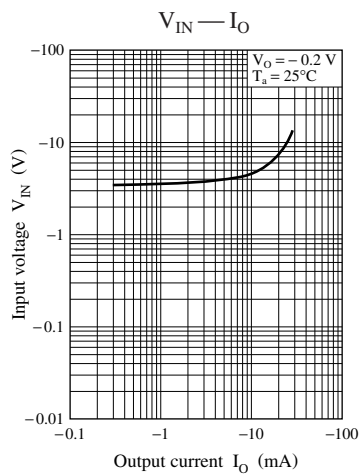
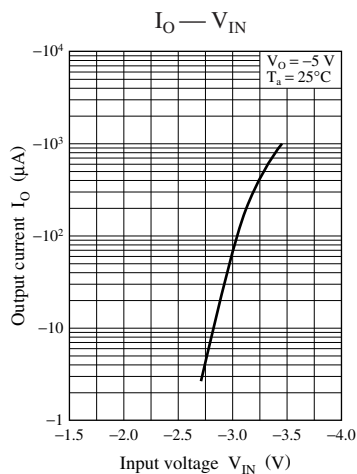
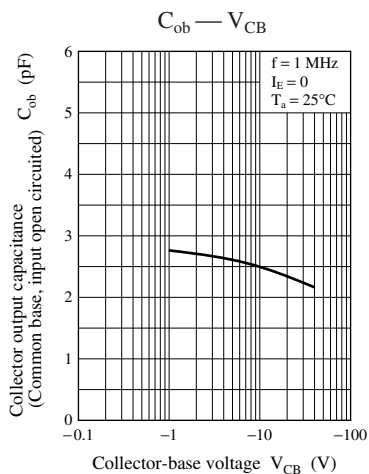
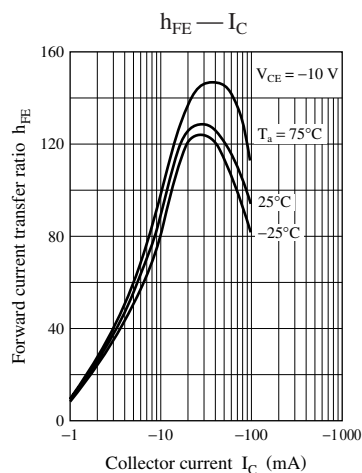
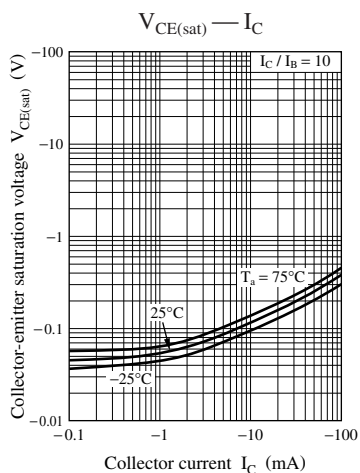
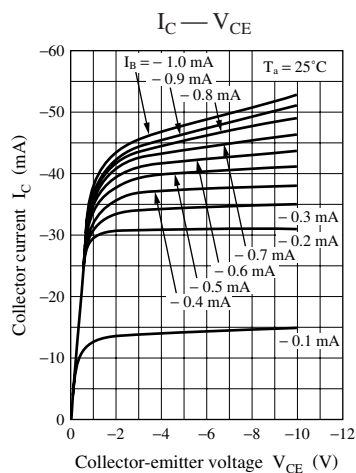


Characteristics charts of UNR5119

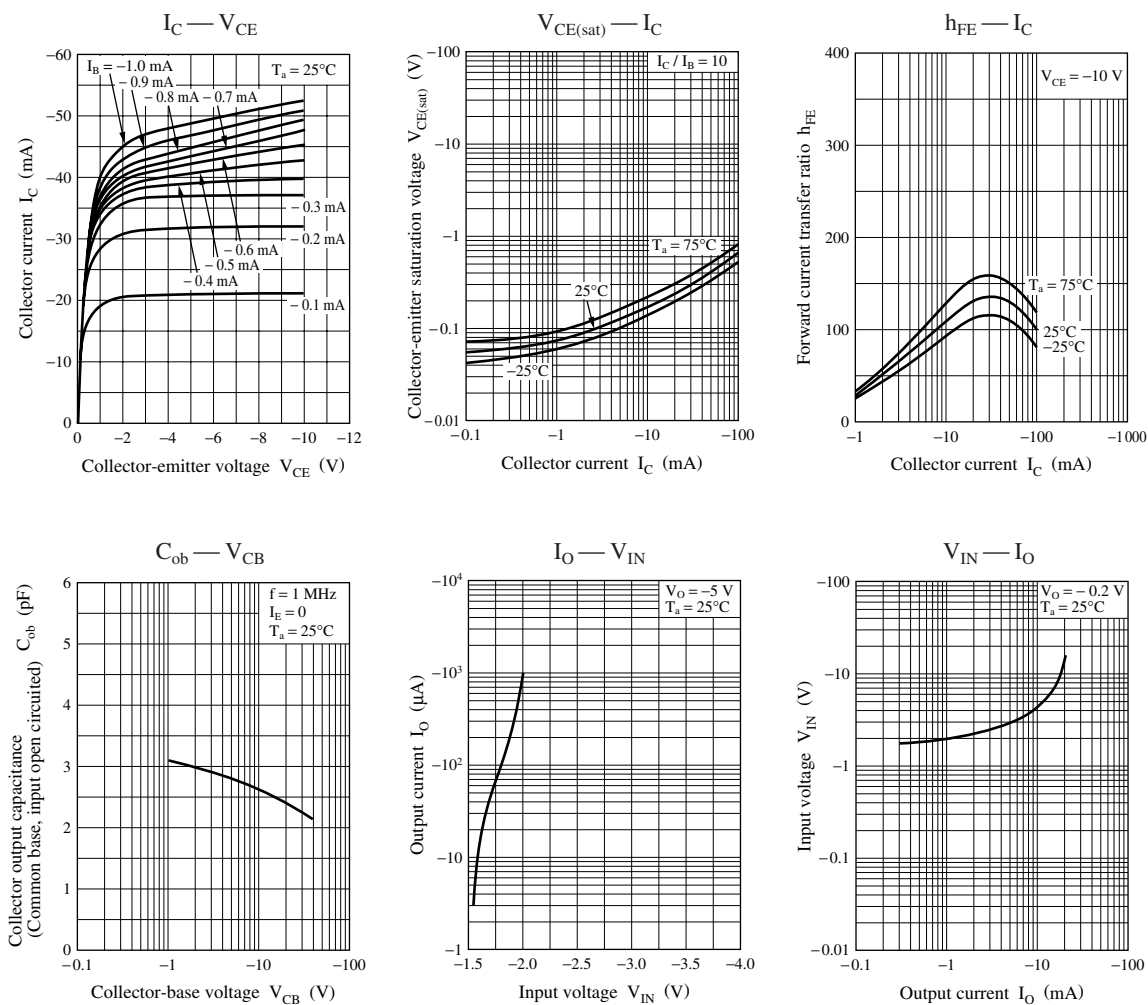




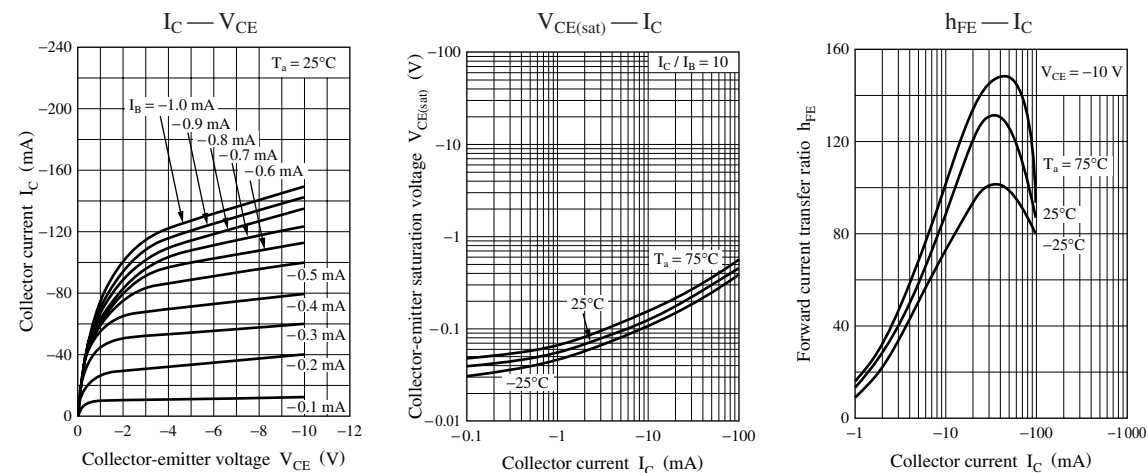
Characteristics charts of UNR511D

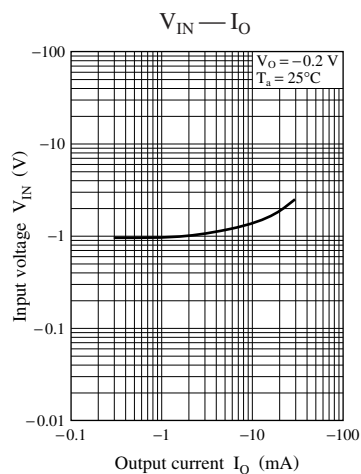
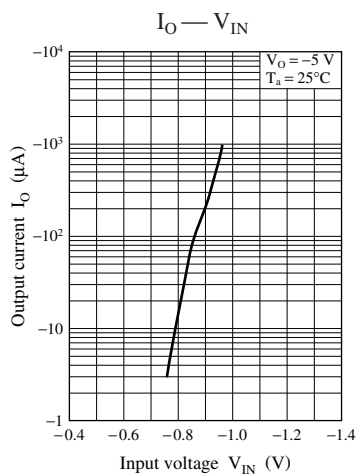
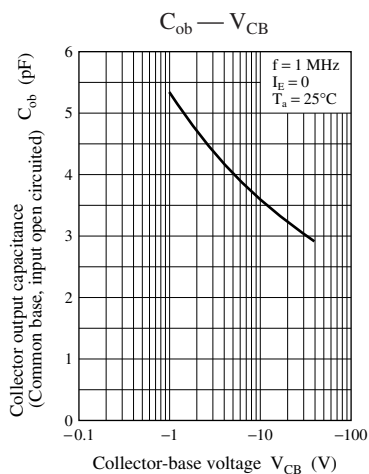


Characteristics charts of UNR511E

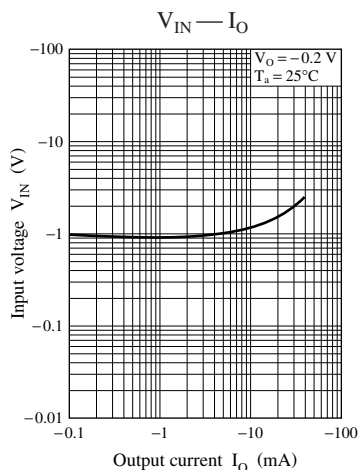
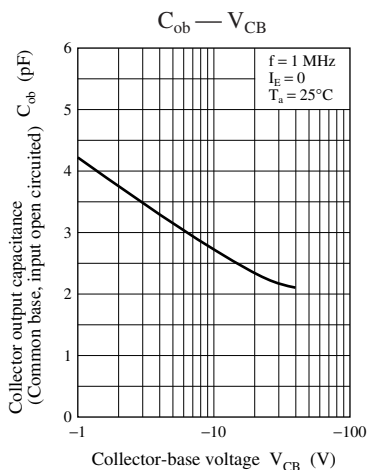
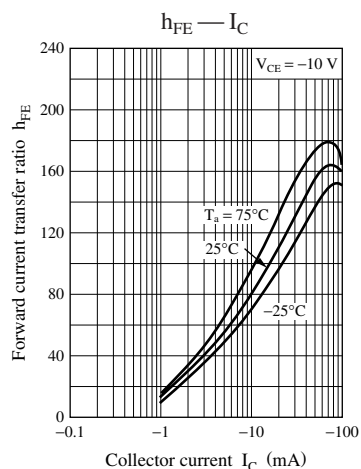
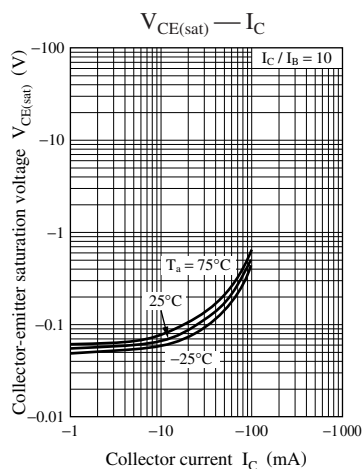
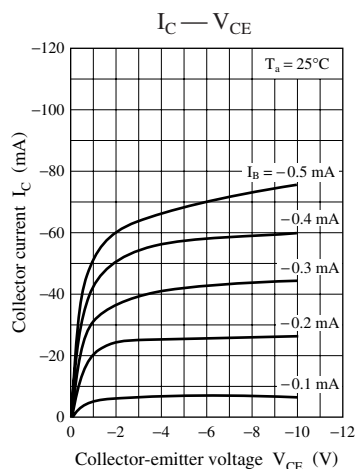


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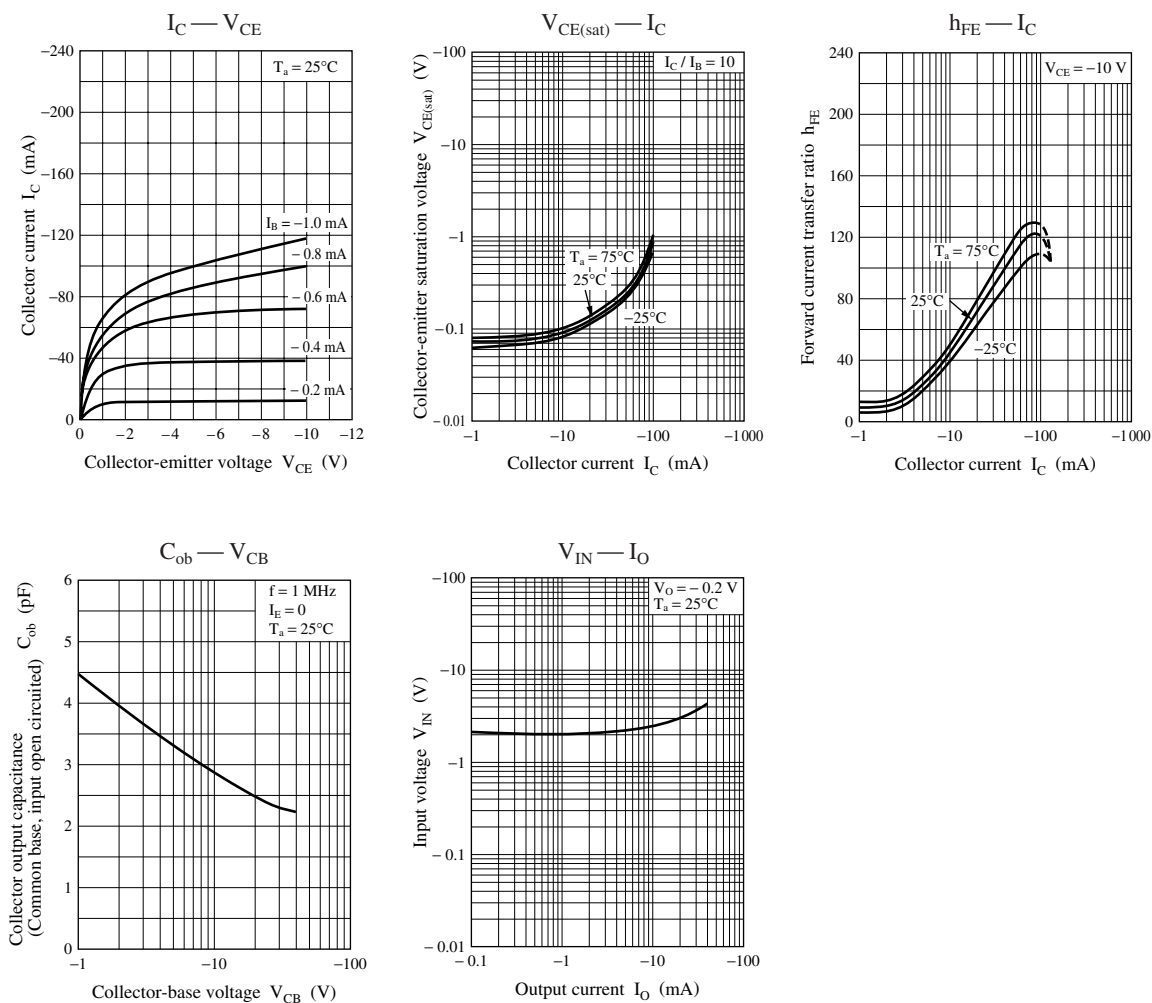




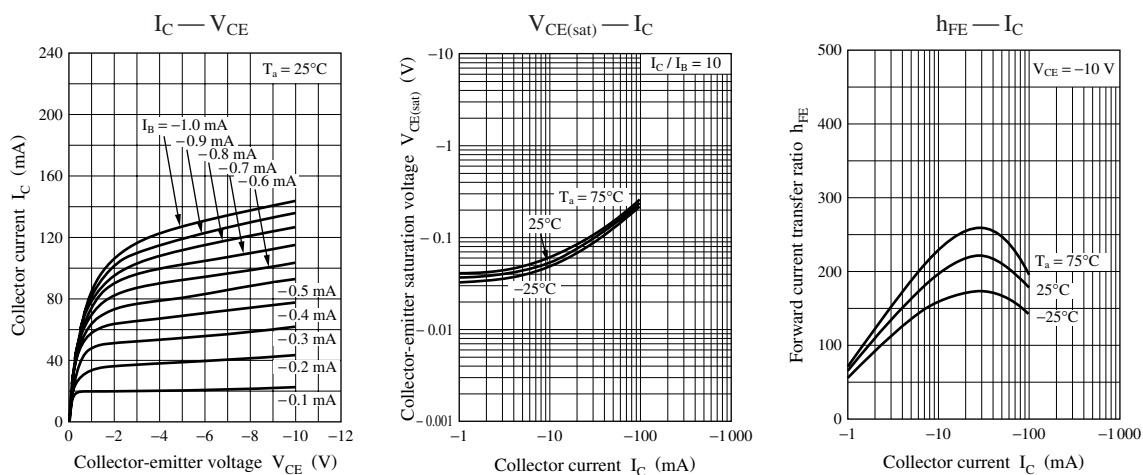
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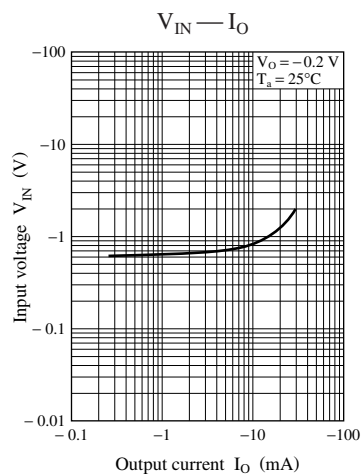
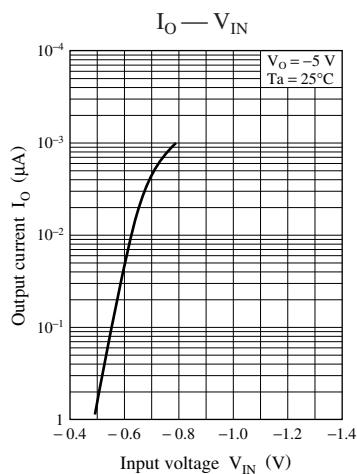
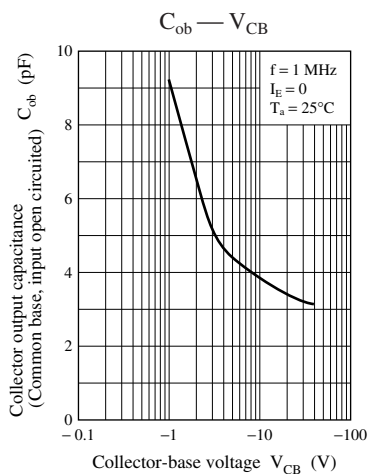


Characteristics charts of UNR511L

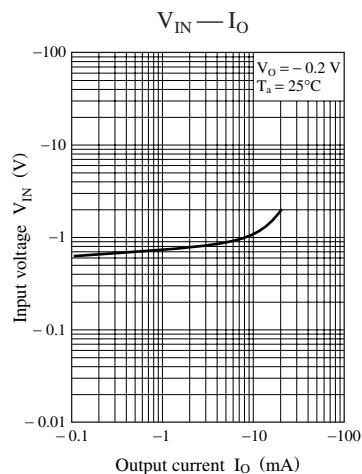
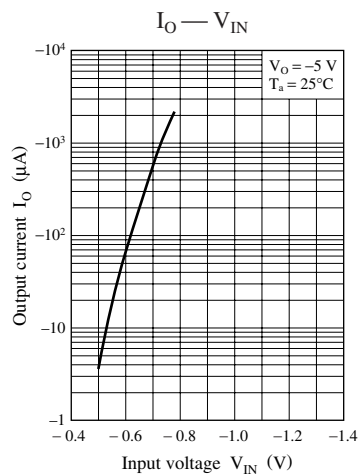
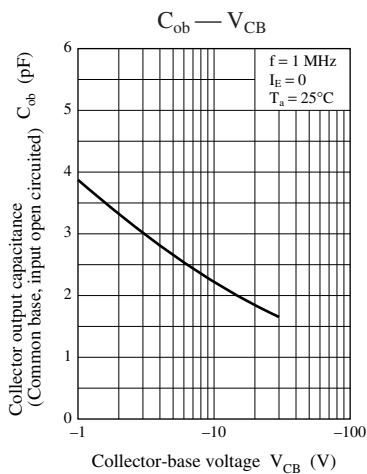
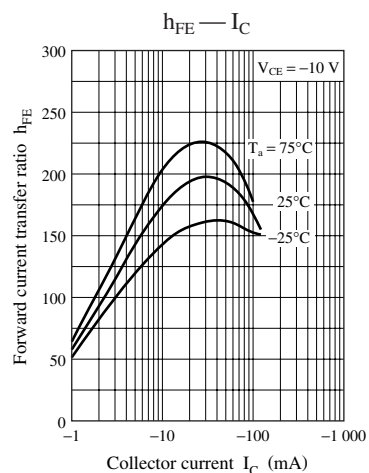
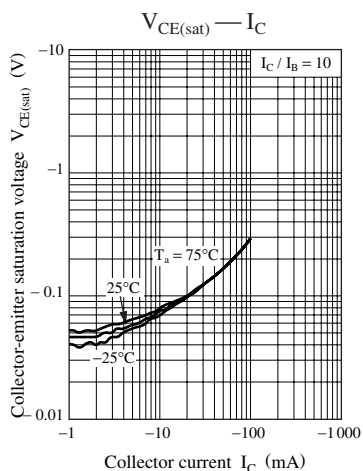
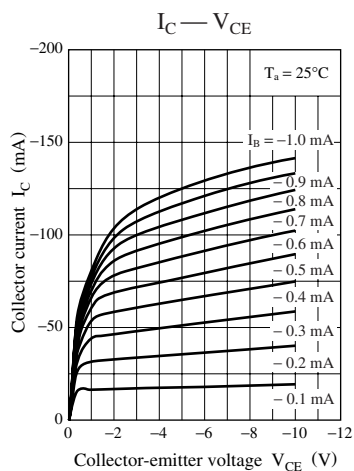


Characteristics charts of UNR511M

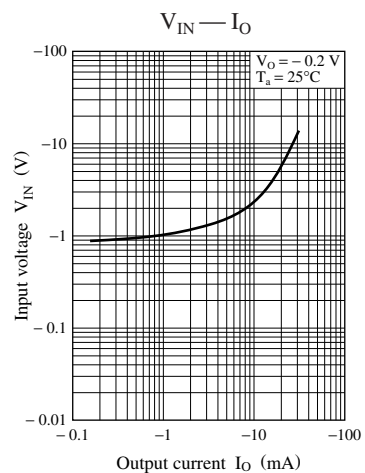
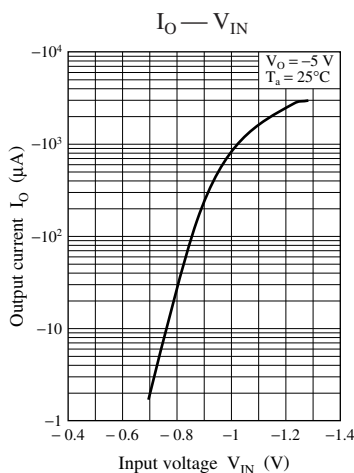
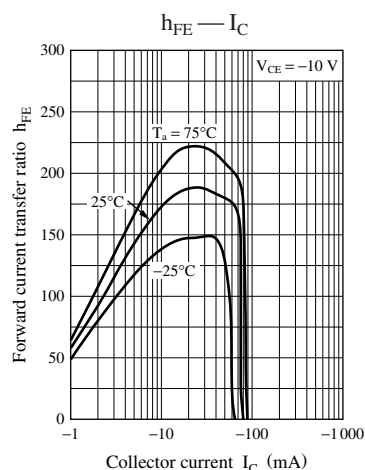
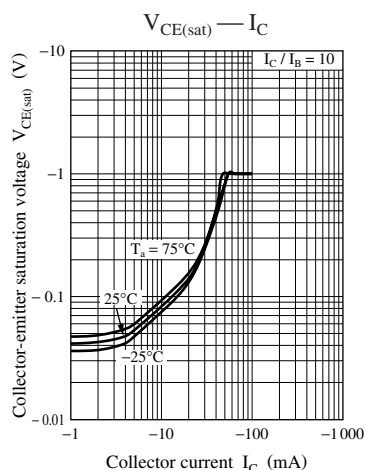
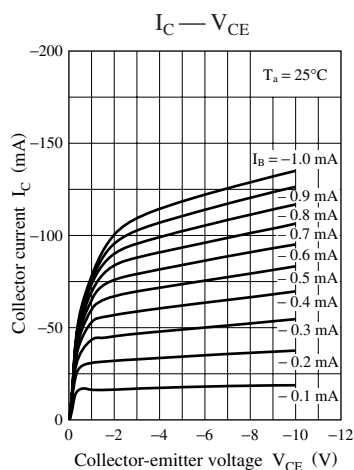




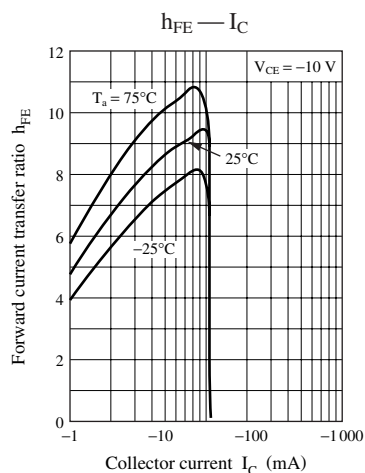
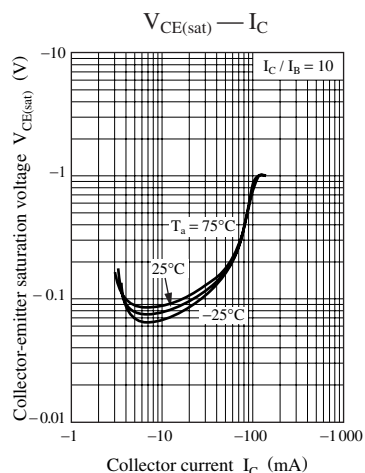
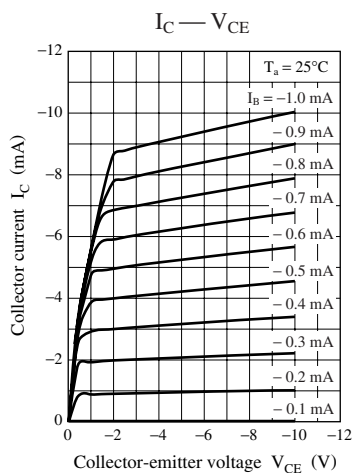
Characteristics charts of UNR511N

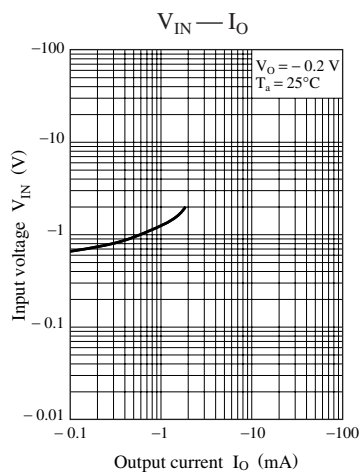
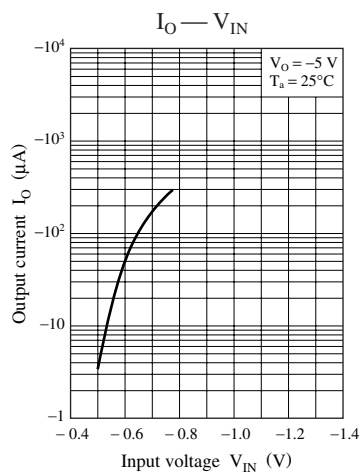


Characteristics charts of UNR511T

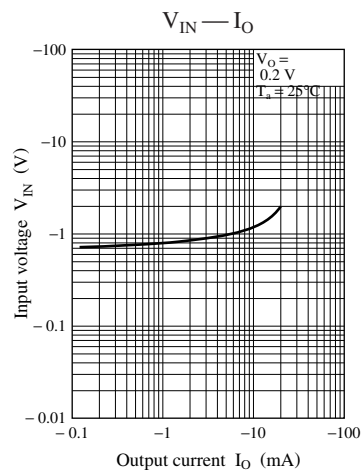
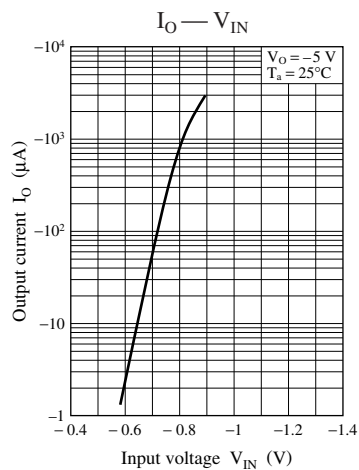
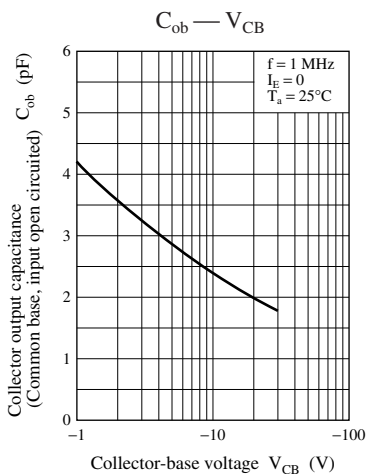
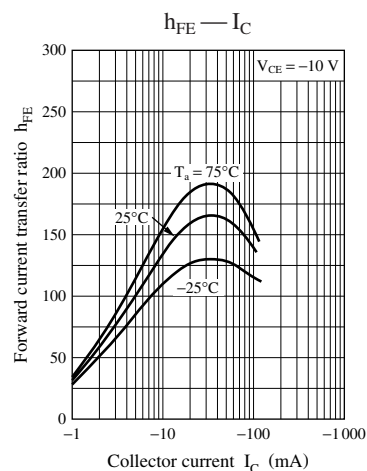
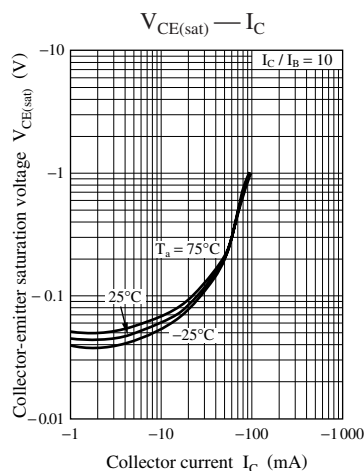
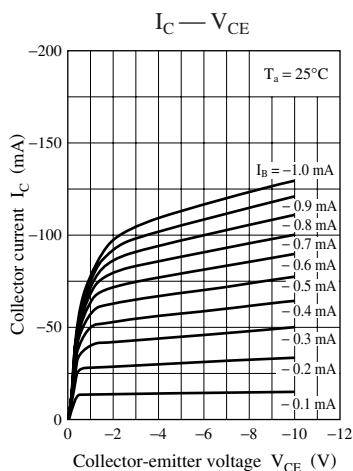


Characteristics charts of UNR511V





Characteristics charts of UNR511Z



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